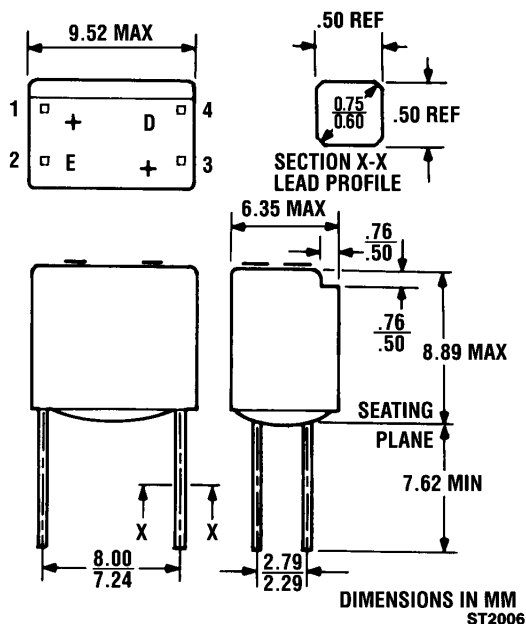


PACKAGE DIMENSIONS

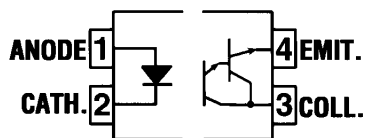


DESCRIPTION

The H24B series consists of a gallium arsenide infrared emitting diode coupled with a silicon phototransistor. The devices are housed in a low-cost plastic package with lead spacing compatible with a dual in-line package.

FEATURES

- 4-pin configuration
- Small package size and low cost
- UL recognized-file E51868
- High current transfer ratio



ST4004

Equivalent Circuit

ABSOLUTE MAXIMUM RATINGS

TOTAL PACKAGE

Storage temperature -55°C to 85°C
Operating temperature -55°C to 85°C
Lead solder temperature 260°C for 5 sec

INPUT DIODE

Power dissipation (25°C ambient) 100 mW
Derate linearly (above 25°C) $1.67\text{ mW}/^{\circ}\text{C}$
Continuous forward current 60 mA
Peak forward current ($1\text{ }\mu\text{s}$ pulse, 300pps) 3 A
Reverse voltage 4 V

DETECTOR

Power dissipation (at 25°C ambient) 150 mW
Derate linearly (above 25°C ambient) $2.5\text{ mW}/^{\circ}\text{C}$
 V_{CEO} 30 V
 V_{ECO} 7 V
Continuous forward current 100 mA